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RF & MICROWAVE TRANSISTORS
VHF-UHF CLASS C WIDE BAND

- FREQUENCY 130 TO 400MHz
- VOLTAGE 28V
- POWER OUT 2.5 TO 13.5W
- HIGH POWER GAIN
- HIGH EFFICIENCY
- CLASS C TRANSISTORS
- COMMON EMITTER



TO 60 (M137)

ORDER CODE

SD1050
 SD1070
 SD1075

BRANDING

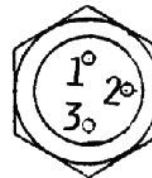
2N3375
 2N3632
 2N3733

DESCRIPTION

This line of silicon epitaxial NPN planar high frequency transistors employs a multi emitter electrode design. This feature together with a heavily diffused base matrix located between the individual emitters results in high RF current handling capability, high power gain, low base resistance and low output capacitance. These transistors are intended for Class A, B, or C amplifier, oscillator or frequency multiplier circuits and are specifically designed for operation in the VHF-UHF region.

Device	Package
2N3375	TO 60
2N3632	TO 60
2N3733	TO 60

PIN CONNECTION



S882N3375-01

1 emitter
 2 base

3 collector

2N3375/2N3632/2N3733

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	2N3375	2N3632	2N3733	Unit
V_{CBO}	Collector to Base Voltage	65	65	65	V
V_{CEO}	Collector to Emitter Voltage	40	40	40	V
V_{EBO}	Emitter to Base Voltage	4.0	4.0	4.0	V
$I_{C(max)}$	Continuous Collector Current	1.5	3.0	3.0	A
P_D	Total Dissipation at 25°C Stud	11.6	23.0	23.0	V
T_j	Junction Temperature	200	200	200	°C
T_{stg}	Storage Temperature	- 65 to 150	- 65 to 150	- 65 to 150	°C

		2N3375	2N3632	2N3733	
$R_{th(j-c)}$	Junction-case Thermal Resistance	15.0	7.6	7.6	°C

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$)

STATIC

Symbol	Test Conditions		2N3375			2N3632			2N3733			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
BV_{CBO}	$I_C = 0.5mA$	$V_{BE} = 0$	65			65			65			V
BV_{CEO}	$I_C = 200mA$	$I_B = 0$	40			40			40			V
BV_{EBO}	$I_E = 0.25mA$	$I_C = 0$	4	($I_E = 0.1mA$)		4			4			V
I_{CEO}	$V_{CB} = 30V$	$I_E = 0$			0.1			0.25			0.25	mA
H_{FE}	$V_{CE} = 5V$	$I_C = 250mA$	10			5	($I_C = 1A$)		10			

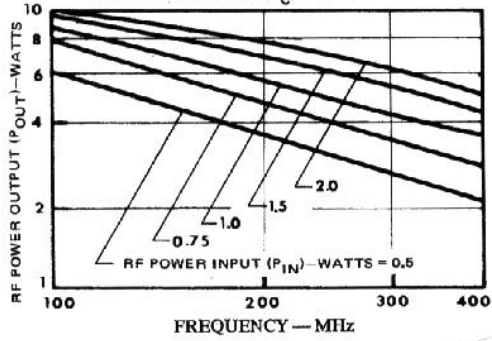
DYNAMIC

Symbol	Test Conditions		2N3375			2N3632			2N3733			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
P_O	$F = 175MHz$ Class C	$V_{CE} = 28V$				13.5						W
P_O	$F = 400MHz$	$V_{CC} = 28V$	3						10			W
G_P	$F = 175MHz$	$V_{CC} = 28V$				5.8						dB
G_P	$F = 400MHz$	$V_{CC} = 28V$	4.8						4.0			dB
η_C	$F = 175MHz$	$V_{CC} = 28V$				70						%
η_C	$F = 400MHz$	$V_{CC} = 28V$	40						45			%
C_{OB}	$F = 1MHz$	$V_{CB} = 30V$			10			20			20	pF

APPLICATION INFORMATION (typical curves)

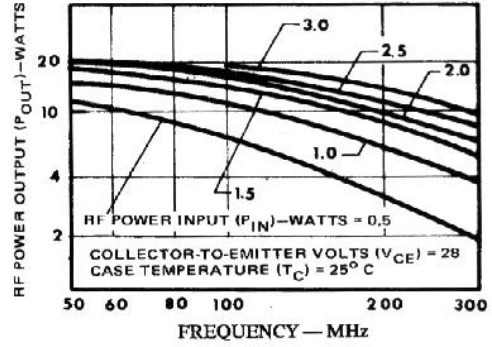
2N3375 POWER OUTPUT VS FREQUENCY

COLLECTOR-TO-EMITTER VOLTS (V_{CE}) = 28
CASE TEMPERATURE (T_C) = 25°C



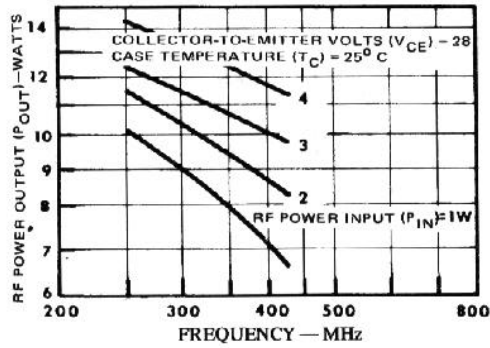
S882N3375-02

2N3632 POWER OUTPUT VS FREQUENCY



S882N3632-04

2N3733 POWER OUTPUT VS FREQUENCY

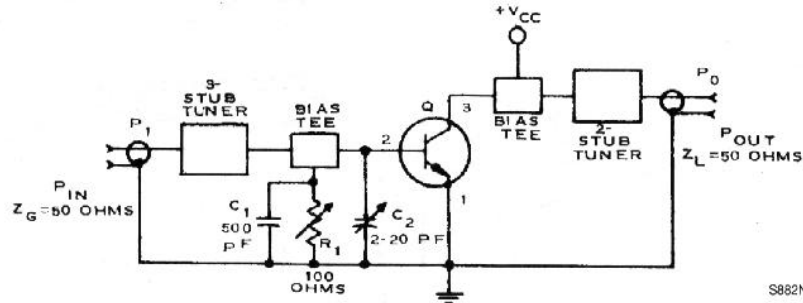


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2N3375/2N3632/2N3733

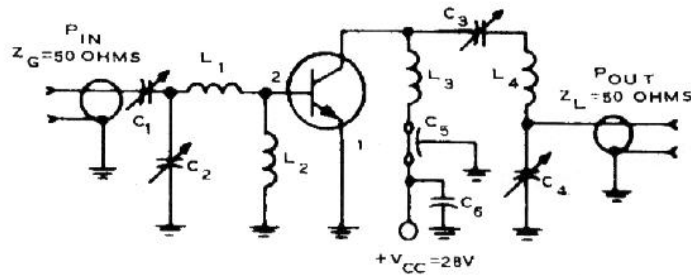
TEST CIRCUITS

2N3375 (400 MHz OPERATION)



S882N3375-02

2N3632 (175MHz OPERATION)



S882N3632-02

2N3632

C₁, C₂, C₃, C₄: 7 - 100pF

C₅: 100pF

C₆: 0.01F, disc ceramic

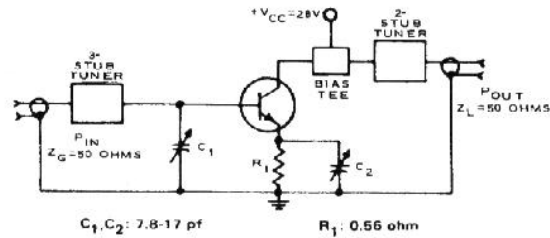
L₁: 1.5 turns No. 16 wire, 3/16" ID, 5/16" long

L₂: Ferrite choke, Z = 450

L₃: 1 turn No. 16 wire, 1/4" ID, 3/8" long

L₄: 2 turns No. 16 wire, 1/4" ID, 1/4" long

2N3733(400MHz OPERATION)



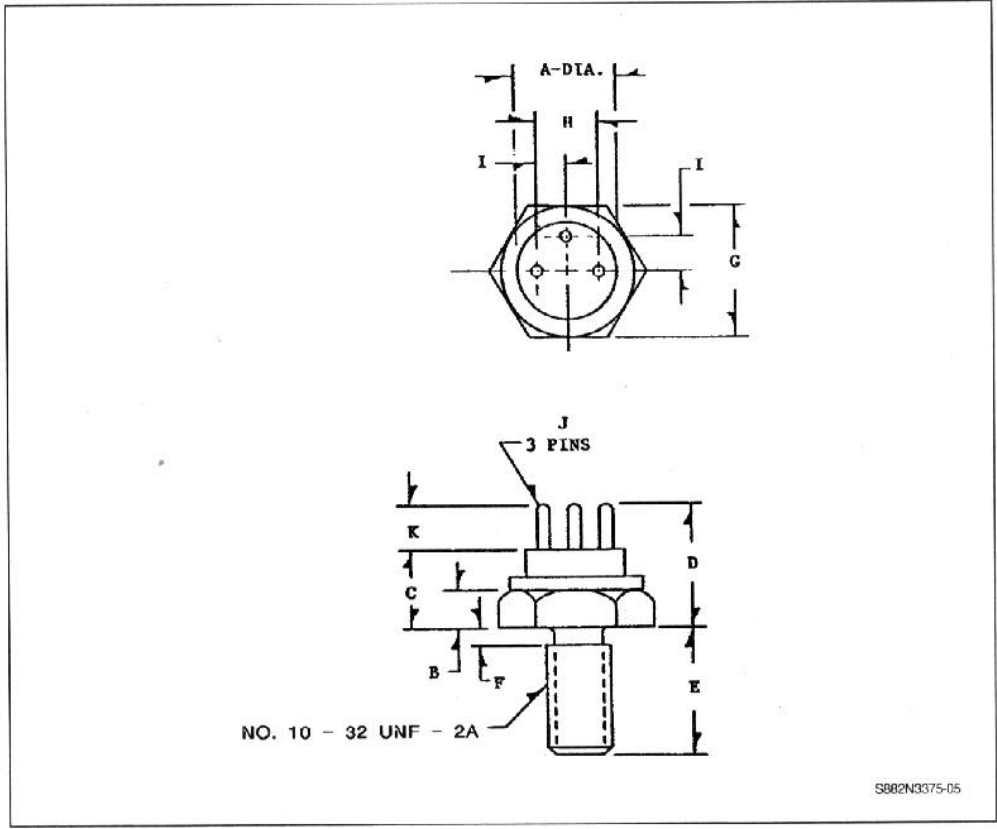
C₁, C₂: 7.8-17 pf

R₁: 0.55 ohm

S882N3733-02

PACKAGE MECHANICAL DATA

TO 60



	Minimum Inches	Maximum Inches
A	.320	.340
B	.110	.135
C	.245	.300
D	.400	.450
E	.420	.455
E	.140	.160

	Minimum Inches	Maximum Inches
F		.078
G	.420	.440
H	.190	.210
I	.095	.105
J	.030	.046
K	.140	.160